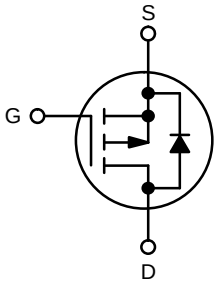
UMW®

FQP47P06

-60V P-Channel MOSFET

Description

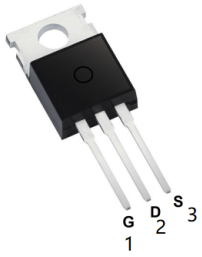
This P−Channel enhancement mode power MOSFET is produced using planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduceon−state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



P−Channel MOSFET

Features

- V_{DS} (V) = -60V
- $R_{DS(on)}$= 26 mΩ (V_{GS} = -10V)
- I_D = - 47A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



ABSOLUTE MAXIMUM RATINGS (T_C= 25°C unless otherwise specified)

Symbol	Parameter		FQP47P06	Unit
V_{DSS}	Drain−Source Voltage		−60	V
I_D	Drain Current	− Continuous (T_C = 25°C)	−47	A
		− Continuous (T_C = 100°C)	−33.2	A
I_{DM}	Drain Current (Note 1)	− Pulsed	−188	A
V_{GSS}	Gate−Source Voltage		±25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		820	mJ
I_{AR}	Avalanche Current (Note 1)		−47	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		16	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		−7.0	V/ns
P_D	Power Dissipation (T_C = 25°C)		160	W
		− Derate above 25°C	1.06	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8” from Case for 5 Seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 0.43 mH, I_{AS} = −47 A, V_{DD} = −25 V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ −47 A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

THERMAL CHARACTERISTICS

Symbol	Characteristic	FQP47P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case, Max.	0.94	°C/W
$R_{\theta CS}$	Thermal Resistance, Case−to−Sink, Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient, Max.	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = −250 μA	−60			V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = −250 μA, Referenced to 25°C		−0.06		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = −60 V, V_{GS} = 0 V			−1	μA
		V_{DS} = −48 V, T_C = 150°C			−10	μA
I_{GSSF}	Gate−Body Leakage Current, Forward	V_{GS} = −25 V, V_{DS} = 0 V			−100	nA
I_{GSSR}	Gate−Body Leakage Current, Reverse	V_{GS} = 25 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = −250 μA	−1.1	-1.8	−2.5	V
$R_{DS(on)}$	Static Drain−Source On−Resistance	V_{GS} = −10 V, I_D = −23.5 A		21	26	mΩ
g_{FS}	Forward Transconductance	V_{DS} = −30 V, I_D = −23.5 A (Note 4)		21		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = −25 V, V_{GS} = 0 V, f = 1.0 MHz		2800	3600	pF
C_{oss}	Output Capacitance			1300	1700	pF
C_{rss}	Reverse Transfer Capacitance			320	420	pF
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn−On Delay Time	V_{DD} = −30 V, I_D = −23.5 A, R_G = 25 Ω (Note 4, 5)		50	110	ns
t_r	Turn−On Rise Time			450	910	ns
$t_{d(off)}$	Turn−Off Delay Time			100	210	ns
t_f	Turn−Off Fall Time			195	400	ns
Q_g	Total Gate Charge	V_{DS} = −48 V, I_D = −47 A, V_{GS} = −10 V (Note 4, 5)		84	110	nC
Q_{gs}	Gate−Source Charge			18		nC
Q_{gd}	Gate−Drain Charge			44		nC
DRAIN−SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATING						
I_S	Maximum Continuous Drain−Source Diode Forward Current				−47	A
I_{SM}	Maximum Pulsed Drain−Source Diode Forward Current				−188	A
V_{SD}	Drain−Source Diode Forward Voltage	V_{GS} = 0 V, I_S = −47 A			−4.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = −47 A, dI_F / dt = 100 A/μs (Note 4)		130		ns
Q_{rr}	Reverse Recovery Charge			0.55		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse width ≤ 300 μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

TYPICAL CHARACTERISTICS

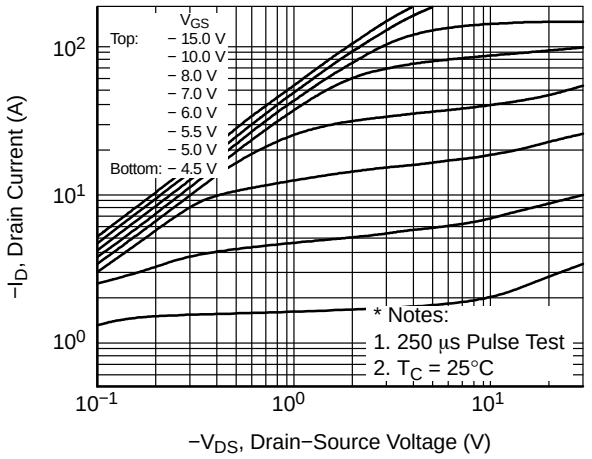


Figure 1. On−Region Characteristics

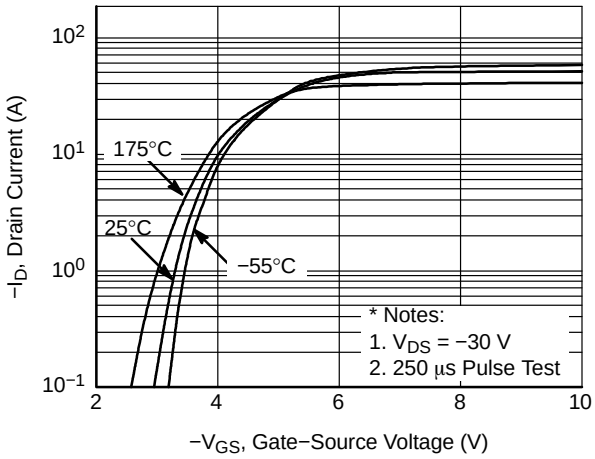


Figure 2. Transfer Characteristics

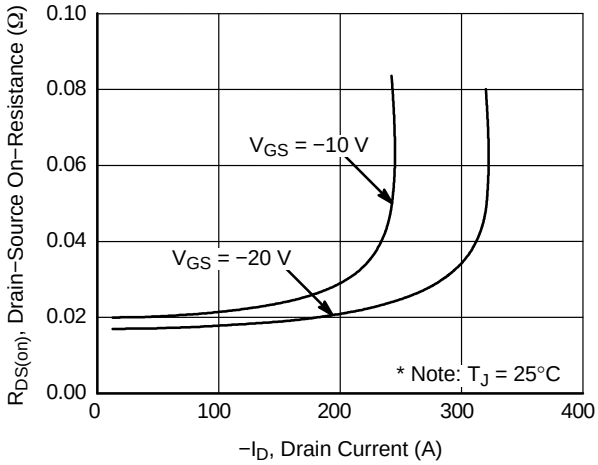


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

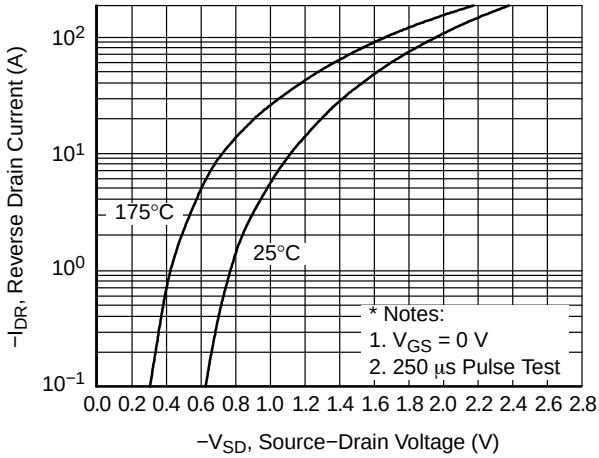


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

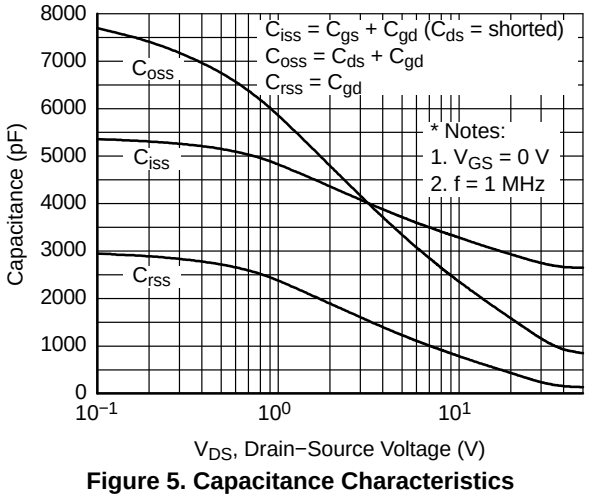


Figure 5. Capacitance Characteristics

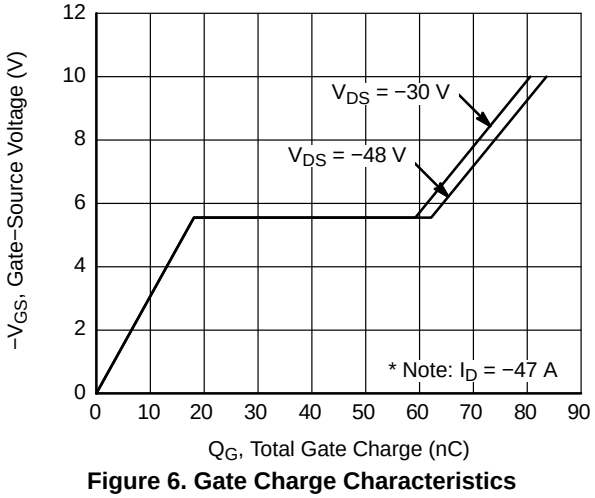


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS (Continued)

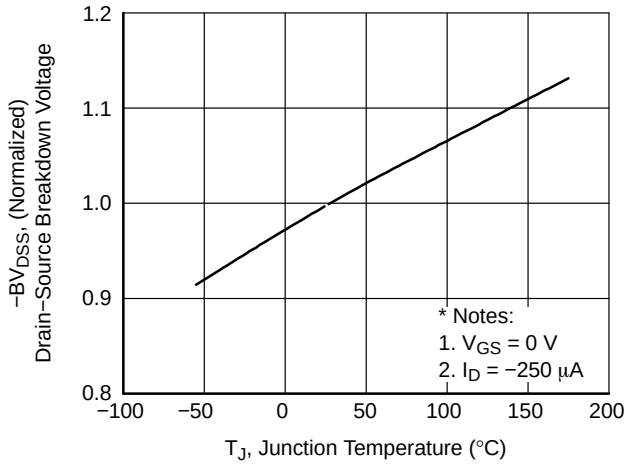


Figure 7. Breakdown Voltage Variation vs. Temperature

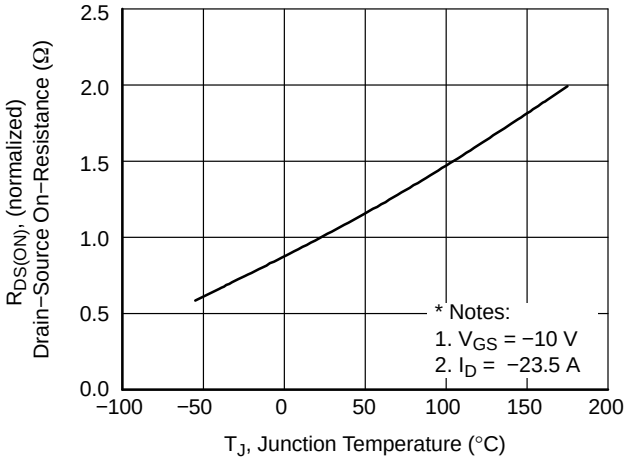


Figure 8. On−Resistance Variation vs. Temperature

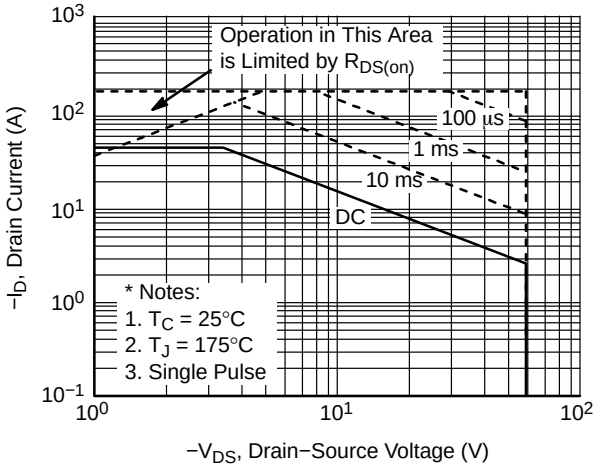


Figure 9. Maximum Safe Operating Area

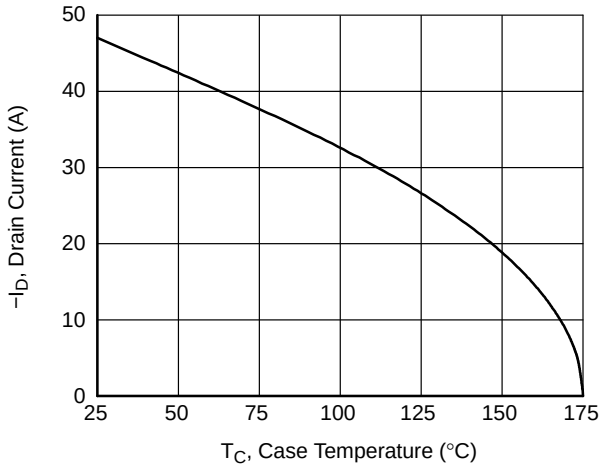


Figure 10. Maximum Drain Current vs. Case Temperature

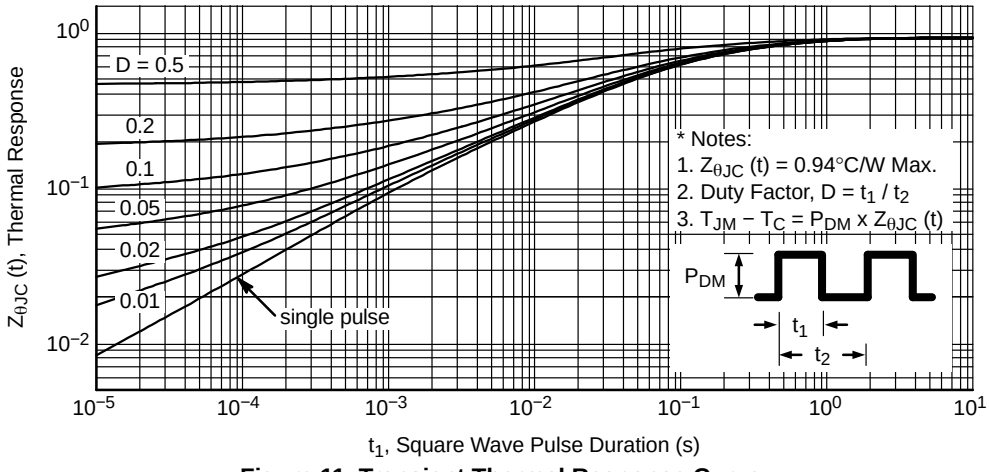


Figure 11. Transient Thermal Response Curve

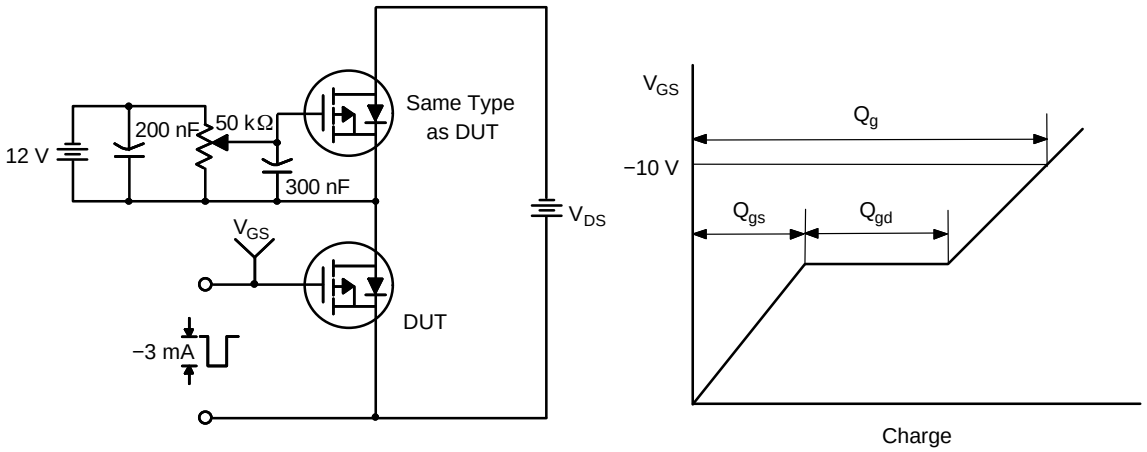


Figure 12. Gate Charge Test Circuit & Waveform

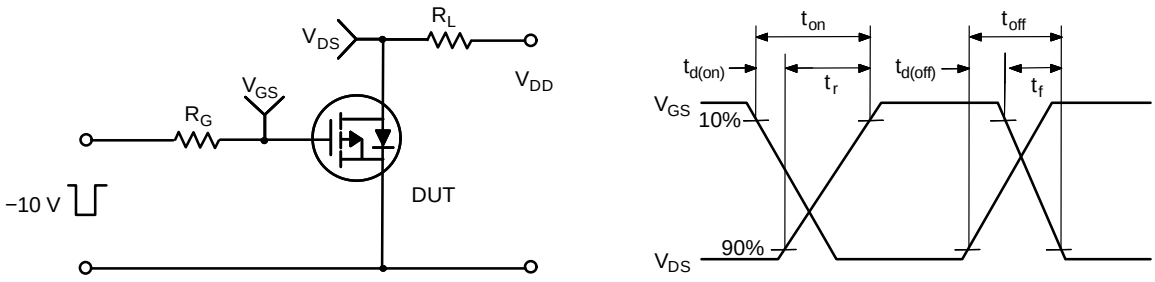


Figure 13. Resistive Switching Test Circuit & Waveforms

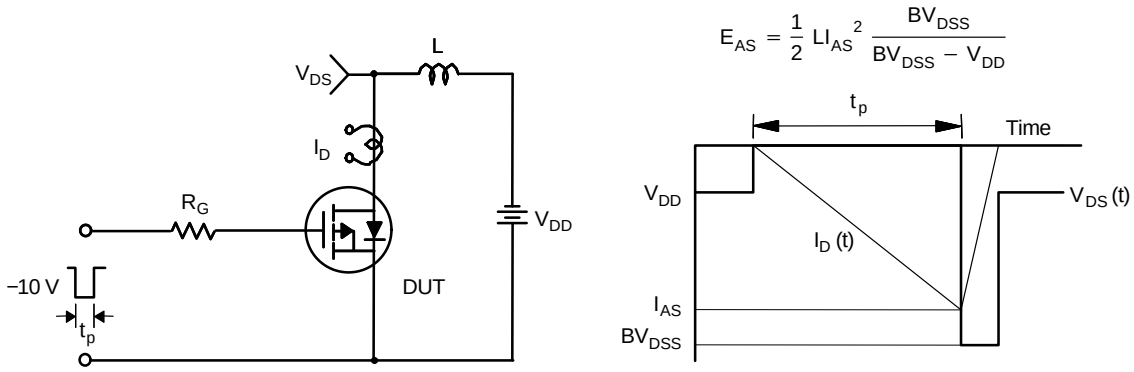


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

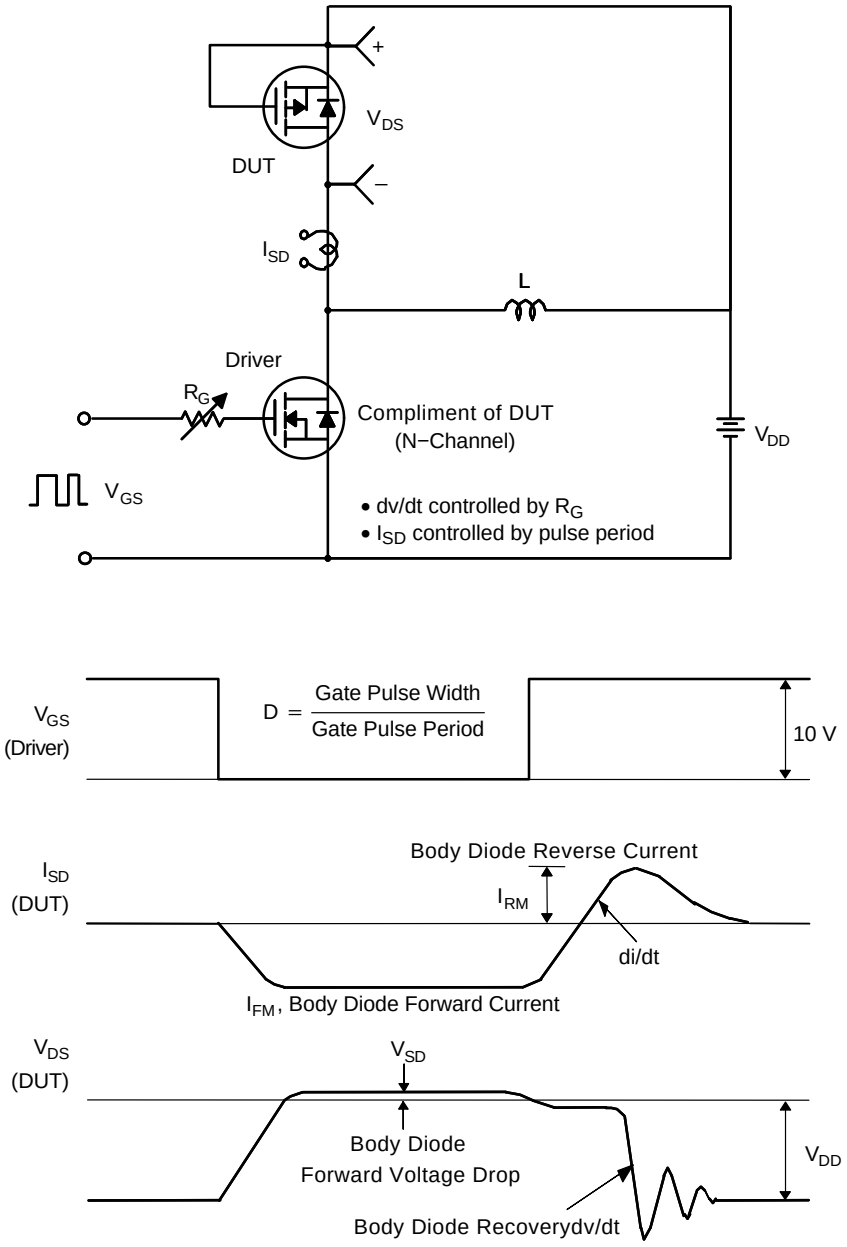
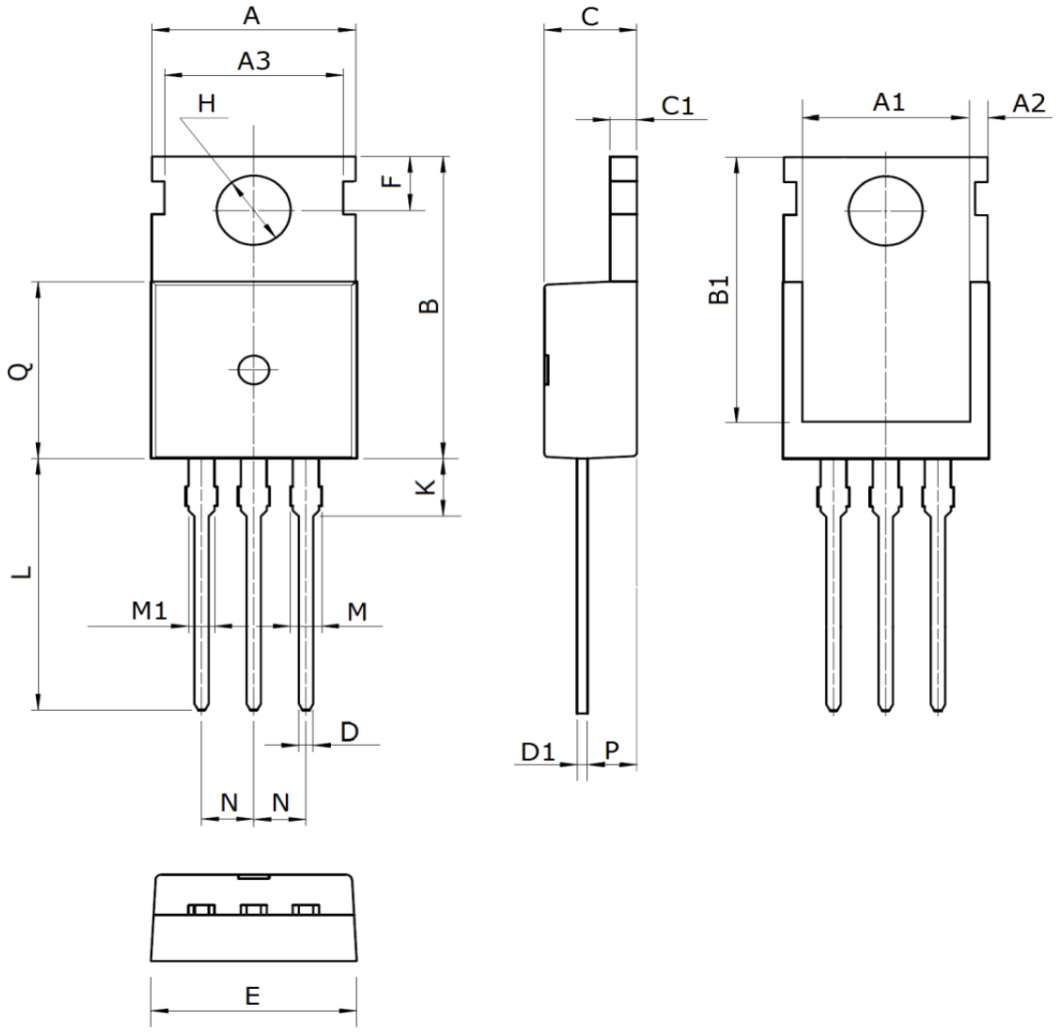


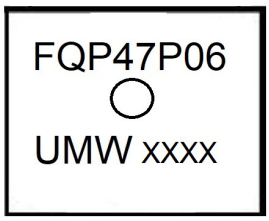
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Package Mechanical Data TO-220



Symbol	Dimensions （mm）	Symbol	Dimensions (mm)	Symbol	Dimensions (mm)
A	10.0±0.3	C1	1.3±0.2	L	13.2±0.4
A1	8.0±0.2	D	0.8±0.2	M	1.38±0.1
A2	0.94±0.1	D1	0.5±0.1	M1	1.28±0.1
A3	8.7±0.1	E	10.0±0.3	N	2.54(typ)
B	15.6±0.4	F	**2.8±0.1**	P	2.4±0.3
B1	**13.2±0.2**	H	3.6±0.1	Q	**9.15±0.25**
C	**4.5±0.2**	K	3.1±0.2		

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FQP47P06	TO-220	1000	Tube and box

单击下面可查看定价，库存，交付和生命周期等信息

>>UMW(友台半导体)